

### **Current Mirror**

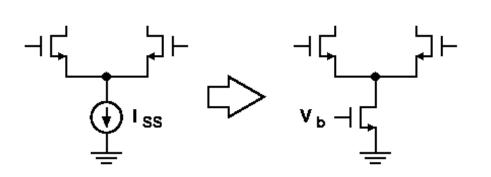
## Outline

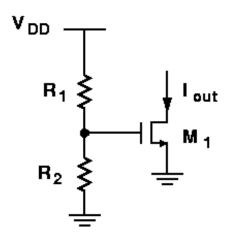
- 1. Basic Current Mirrors
- 2. Cascode Current Mirrors
- 3. Active Current Mirrors

#### **Current Source Issues**

#### Design issues

- Voltage headroom.
- Output impedance.
- Supply, process, and temperature dependence.
- Matching.

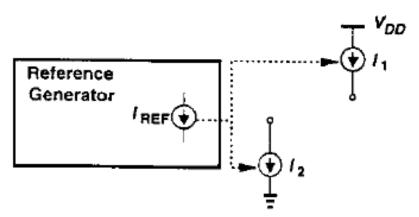


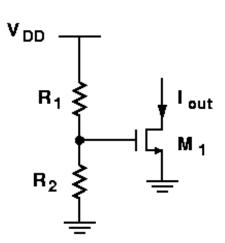


$$I_{out} \approx \frac{1}{2} \mu_n C_{ox} \frac{W}{L} \left( \frac{R_2}{R_1 + R_2} V_{DD} - V_{TH} \right)^2$$

# Current Source with Constant V<sub>b</sub>

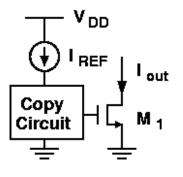
- Depending on supply, process, and temperature.
- The threshold voltage may vary by 100 mV from wafer to wafer.
- Both  $\mu_n$  and  $V_{TH}$  exhibit temperature dependence.
- The issue becomes more severe as the device is biased with a smaller overdrive voltage. (200mV  $V_{ov}$ , 50mV  $\Delta V_{TH}$  cause 44% error)
- If the gate-source voltage of a MOSFET is precisely defined, then its drain current is not.
  - → Copying currents from a reference.

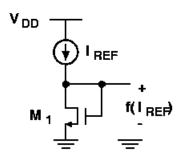




#### **Basic Current Mirror**

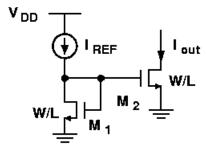
• For  $I_{out} = I_{REF}$ 





$$V_{GS} = f^{-1}(I_{REF})$$

$$ff^{-1}(I_{REF}) = I_{REF}$$



$$I_{REF} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right)_1 \left(V_{GS} - V_{TH}\right)^2$$

$$I_{out} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right)_2 \left(V_{GS} - V_{TH}\right)^2$$

$$\frac{I_{out}}{I_{REF}} = \frac{\left(W/L\right)_2}{\left(W/L\right)_1}$$

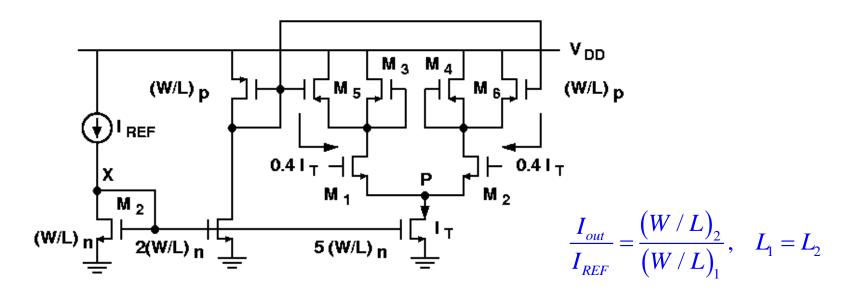
 It allows precise copying of the current with no dependence on process and temperature.

### Current Mirror: Sink & Source

 Current mirrors employ the same length for all of the transistors so as to minimize errors due to the side diffusion of the source and drain areas.

$$L_{eff} = L_{drawn} - 2L_{D}$$

Current ratio by only scaling the width of transistors.



# Current Mirror with r<sub>o</sub>

• Channel length modulation effect results in significant error in copying currents.  $\mathbf{v}_{pp}$ 

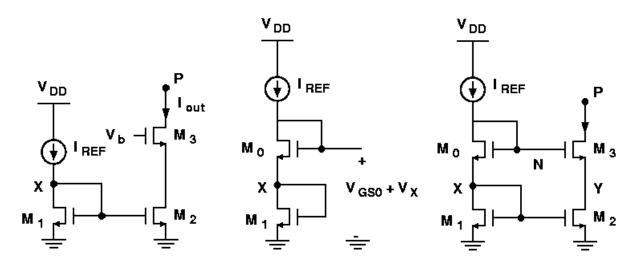
$$I_{D1} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right) \left(V_{GS} - V_{TH}\right)^2 \left(1 + \lambda V_{DS1}\right), \quad I_{D2} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right) \left(V_{GS} - V_{TH}\right)^2 \left(1 + \lambda V_{DS2}\right)$$

- As  $\frac{I_{D2}}{I_{D1}} = \frac{(W/L)_2}{(W/L)_1} \frac{1 + \lambda V_{DS2}}{1 + \lambda V_{DS1}}$ , for  $I_{D1} = I_{D2}$ ,  $V_{DS1}$  must be equal to  $V_{DS2}$ .
- Use cascode structure to improve the ratio accuracy of current mirror.

## Outline

- 1. Basic Current Mirrors
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- 3. Active Current Mirrors

### Cascode Current Mirror



•  $V_b$  is chosen such that  $V_Y = V_X$ .

$$V_b - V_{GS3} = V_X$$
,  $V_b = V_{GS3} + V_X$ ,  $V_N = V_{GS0} + V_X$  if  $\frac{(W/L)_3}{(W/L)_0} = \frac{(W/L)_2}{(W/L)_1}$ , then  $V_{GS0} = V_{GS3}$  and  $V_X = V_Y$ 

 Such accuracy is obtained at the cost of the voltage headroom consumed by M<sub>3</sub>.

### Cascode Current Mirror

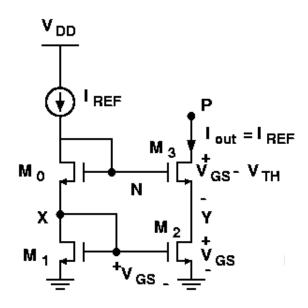
The minimum allowable voltage at node P is equal to

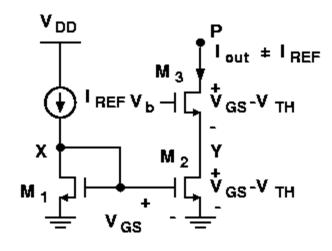
$$\begin{split} V_{N} - V_{TH} &= V_{GS1} + V_{GS0} - V_{TH} \\ &= \left(V_{GS1} - V_{TH}\right) + \left(V_{GS0} - V_{TH}\right) + V_{TH} \end{split}$$

- The voltage of  $V_N = V_{GS1} + V_{GS0}$
- For  $M_2$  to be in saturation region,  $V_b$  can be chosen as low as

$$V_b = V_{GS3} + V_{DS2}$$

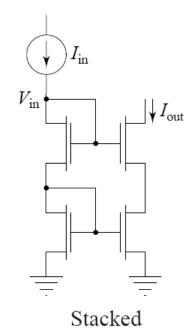
• But the output current does not accurately track  $I_{RFF}$ .

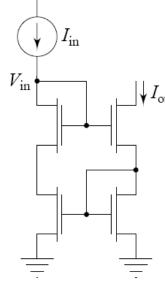




#### Cascode Current Mirror

- Each of these mirrors is self biasing, has a high output impedance, and provides a low systematic transfer error.
- Each requires an input voltage of two diode drops.
- Each has an output compliance voltage of a diode drop plus a saturation voltage.
- Neither is suitable for use with a low power supply voltage.





Super Wilson

- To eliminate the accuracy-headroom trade-off.
- For M2 to be saturated

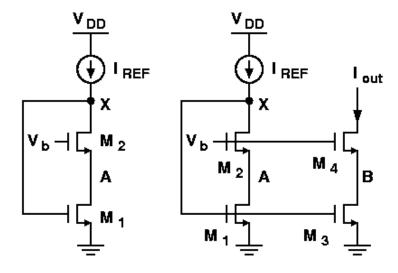
$$V_b - V_{TH2} \le V_X (= V_{GS1})$$

For M1 to be saturated

$$V_{GS1} - V_{TH1} \le V_A (= V_b - V_{GS2})$$

Thus

$$V_{GS2} + (V_{GS1} - V_{TH1}) \le V_b \le V_{GS1} + V_{TH2}$$



A solution exist if

$$V_{GS2} + (V_{GS1} - V_{TH1}) \le V_{GS1} + V_{TH2} \Longrightarrow V_{GS2} - V_{TH2} \le V_{TH1}$$

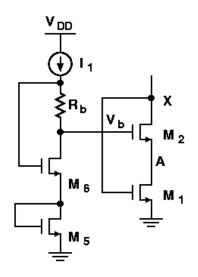
Let

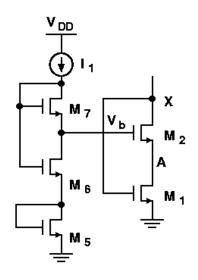
$$V_{GS2} = V_{GS4} \Longrightarrow V_b = V_{GS2} + (V_{GS1} - V_{TH1}) = V_{GS4} + (V_{GS3} - V_{TH3})$$

- Generation of biased voltage V<sub>b</sub>
  - Let 
    $$\begin{split} V_{GS5} \approx V_{GS2} \\ V_{DS6} = V_{GS6} I_1 R_b = V_{DS1} \\ \Rightarrow If \quad V_{GS6} = V_{GS1} \\ \Rightarrow I_1 R_b = V_{TH6} = V_{TH1} \end{split}$$
  - Some inaccuracy arises because M<sub>5</sub> does not suffer from body effect whereas M<sub>2</sub> does.
  - $-I_1R_h$  is not well controlled.
- The diode connected M7 has a large W/L such that

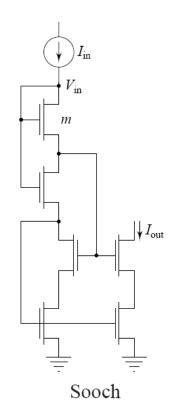
$$\begin{split} V_{GS7} &\approx V_{TH7} \\ V_{DS6} &\approx V_{GS6} - V_{TH7} \\ V_b &= V_{GS5} + V_{GS6} - V_{TH7} \end{split}$$

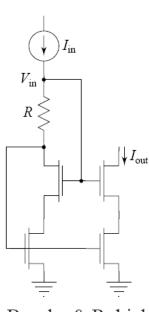
This circuit suffers from similar errors due to body effect.





- All Self biasing, has a high output impedance, and provides a low systematic transfer error.
- Each has an output compliance voltage of two saturation voltages.
- The Sooch mirror requires an input voltage of two diode drops, which makes it unsuitable for low-voltage applications.
- The Brooks-Rybicki mirror requires an input voltage of a diode drop plus a saturation voltage, but requires a different value of *R for every l<sub>in</sub>*.





Brooks & Rybicki

## Wide-Swing Cascode + SF Level Shifter

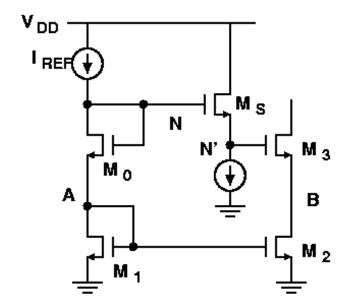
- Shift the gate voltage of M<sub>3</sub> down with respect to V<sub>N</sub> by interposing a source follower.
- Let  $M_s$ 's  $V_{GSs} = V_{TH3}$ ,

$$V_{N'} pprox V_{N} - V_{TH3}$$
 
$$V_{B} = V_{GS1} + V_{GS0} - V_{TH3} - V_{GS3} = V_{GS1} - V_{TH3}$$

M<sub>s</sub> is biased at a very low current density,

$$V_{GSs} - V_{THs} \approx \sqrt{\frac{2I}{\mu_n C_{ox} W / L}}$$

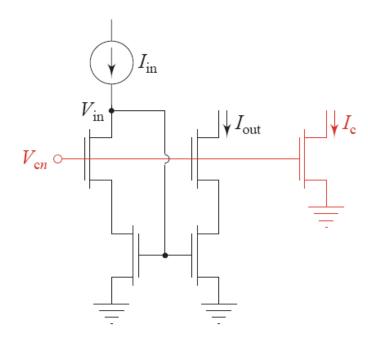
- M<sub>2</sub> is at the edge of the saturation region.
- Substantial current mismatch is introduced for



$$V_{DS2} \neq V_{DS1}$$

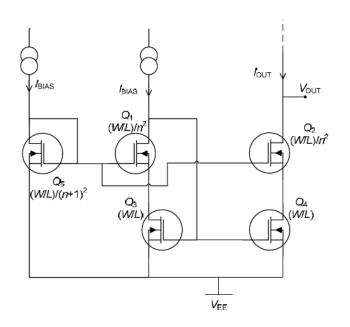
• If the body effect of  $M_0$ ,  $M_S$ , and  $M_3$  is considered, it is difficult to guarantee that M2 operates in saturation.

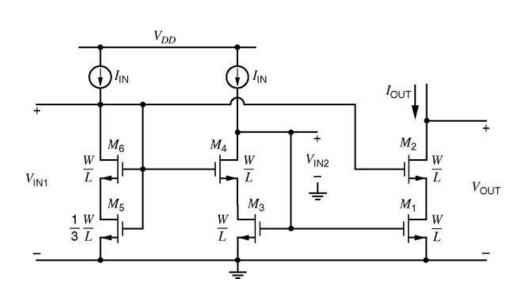
- To facilitate low-voltage operation, we can remove the cascode bias-voltage generation from the input branch.
- The output compliance voltage remains twos saturation voltages.
- The input voltage becomes a diode drop, comparable to that of a simple mirror.
- The optimal value of  $V_{cn}$  depends on  $I_{in}$ , which sometimes requires us to generate  $V_{cn}$  adaptively.



Babanezhad & Gregorian

- $V_{OUT} = V_{DS2} + V_{DS4} = V_{OD2} + V_{OD4}$  and  $V_{OD4} = nV_{OD2}$
- $V_{OUT\;min}=V_{OD2}+nV_{OD2}=(n+1)V_{OD}$ , Often n=1;  $V_{OUT\;min}=2(V_{GS2}-V_t)$

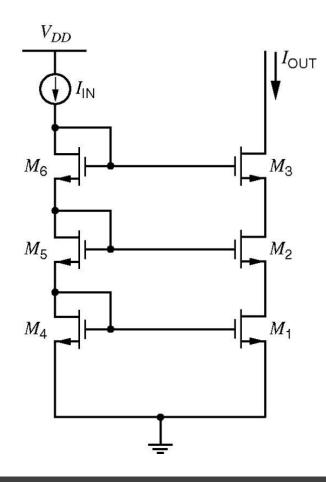




$$V_{IN1} = V_{DS5} + V_{DS6} = V_t + 2V_{OV}$$
  
 $V_{IN2} = V_{GS3} = V_t + V_{OV}$ 

#### Double-Cascode Current Mirror

- Higher output impedance, more current ratio accuracy
- Smaller output swing

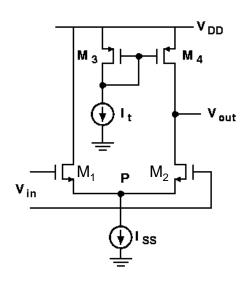


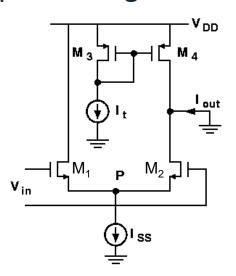
## Outline

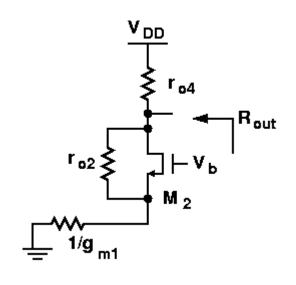
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#### **Active Current Mirror**

Current mirror can also process signals







$$|A_V| = G_m R_{out}$$
  $G_m = \frac{I_{out}}{V_{in}} = \frac{g_{m1} V_{in} / 2}{V_{in}} = \frac{g_{m1}}{2}$ 

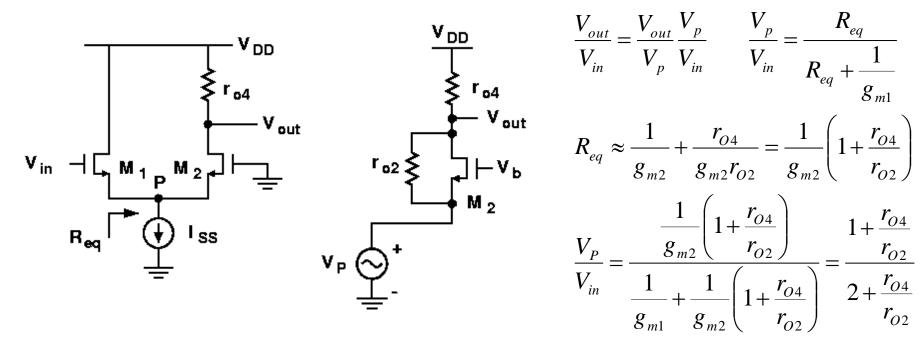
The output impedance looking into the drain of M<sub>2</sub> is

$$(1+g_{m2}r_{O2})(1/g_{m1,2})+r_{O2} = 2r_{O2}+1/g_{m1} \approx 2r_{O2}$$

• Thus,  $R_{out} \approx (2r_{O2}) \| r_{O4} \Rightarrow | A_{v} | \approx \frac{g_{m1}}{2} [(2r_{O2}) \| r_{O4}] \text{ If } r_{O4} \rightarrow \infty \Rightarrow | A_{v} | \approx g_{m1} r_{O2}$ 

#### Active Current Mirror

#### An Alternative Solution



$$\frac{V_{out}}{V_{in}} = \frac{V_{out}}{V_{p}} \frac{V_{p}}{V_{in}} \qquad \frac{V_{p}}{V_{in}} = \frac{R_{eq}}{R_{eq}} + \frac{1}{g_{m1}}$$

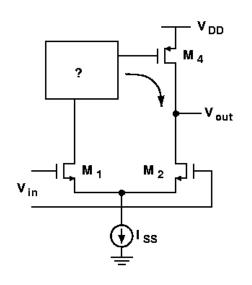
$$R_{eq} \approx \frac{1}{g_{m2}} + \frac{r_{O4}}{g_{m2}r_{O2}} = \frac{1}{g_{m2}} \left(1 + \frac{r_{O4}}{r_{O2}}\right)$$

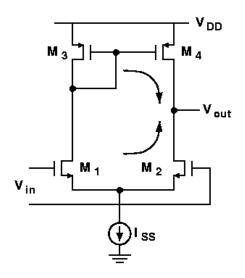
$$\frac{V_{p}}{V_{in}} = \frac{\frac{1}{g_{m2}} \left(1 + \frac{r_{O4}}{r_{O2}}\right)}{\frac{1}{g_{m2}} + \frac{1}{g_{m2}} \left(1 + \frac{r_{O4}}{r_{O2}}\right)} = \frac{1 + \frac{r_{O4}}{r_{O2}}}{2 + \frac{r_{O4}}{r_{O2}}}$$

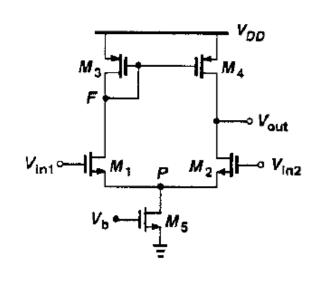
$$\frac{V_{out}}{V_{in}} = \frac{1 + \frac{r_{O4}}{r_{O2}}}{2 + \frac{r_{O4}}{r_{O2}}} \cdot \frac{g_{m2}r_{O2}}{1 + \frac{r_{O2}}{r_{O4}}} = \frac{g_{m2}r_{O2}r_{O4}}{2r_{O2} + r_{O4}} = \frac{g_{m2}}{2} [(2r_{O2}) || r_{O4}]$$

## Differential to Single-Ended Amplifier

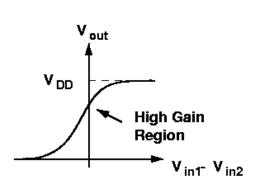
Current combination utilizing current mirror.







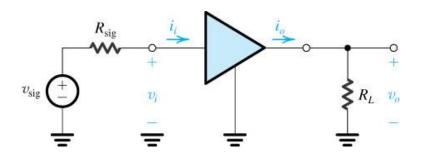
- If  $V_{in1}$  is much more negative than  $V_{in2}$ ,  $M_1$  is off and so are  $M_3$  and  $M_4$ . Both  $M_2$  and  $M_5$  operate in deep triode region.
- For a small  $|V_{in1} V_{in2}|$ ,  $M_1 M_4$  are saturated => high gain
- The minimum input voltage level of  $V_{in2} = V_{GS1,2} + V_{DS5,min}$
- With perfect symmetry,  $V_{out} = V_F = V_{DD} |V_{GS3}|$ .
- But  $V_{out}$  can vary a lot if device mismatches occur.



## **Small-Signal Analysis**

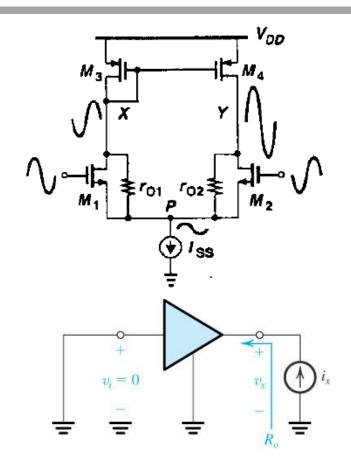
 Node "P" is not a virtual ground since amplitude of V<sub>x</sub> ≠ V<sub>y</sub>

• Find  $G_m$  and  $R_{out}$ ,  $|A_v| = G_m R_{out}$ ,



Short-circuit Transconductance

$$G_m \equiv \frac{\dot{l}_o}{v_i}\bigg|_{R_L=0}$$

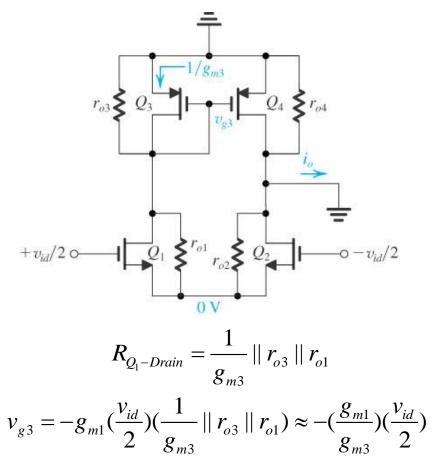


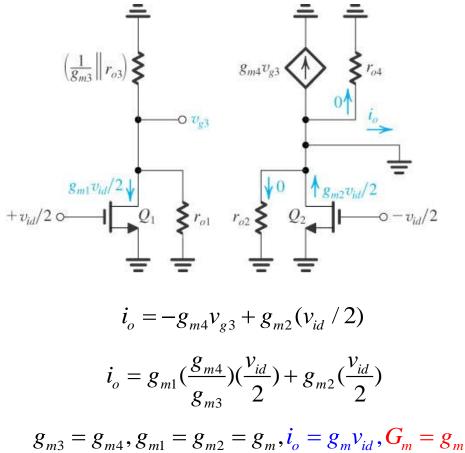
Output resistance of amplifier proper

$$R_o \equiv \frac{v_x}{i_x} \bigg|_{v_i = 0}$$

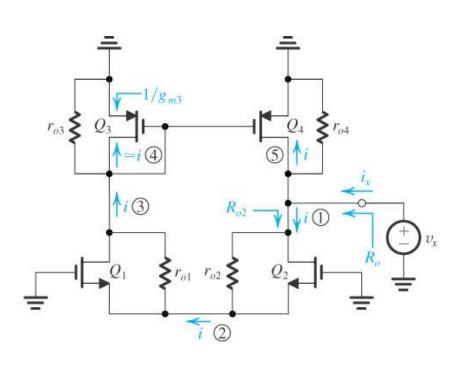
# Transconductance $G_m$

 The impedance from Q1 drain to ground is small, it makes source node as virtual ground.





# Determining the Output Resistance R<sub>o</sub>



$$R_{o2} = r_{o2} + (1 + g_{m2}r_{o2})(1/g_{m1}) \approx 2r_{o2}$$
  
For  $g_{m1} = g_{m2} = g_m$ ,  $g_{m2}r_{o2} >> 1$ 
  
 $\Rightarrow R_{o2} \cong 2r_{o2}$ 

$$i_x = \frac{v_x}{R_{o2}} + \frac{v_x}{r_{o4}}$$

$$R_o = R_{o2} \parallel r_{o4} \cong \frac{1}{2} r_o$$

• 
$$G_m = g_{m1.2} \cong g_m, R_{out} = R_o \cong \frac{1}{2} r_o$$

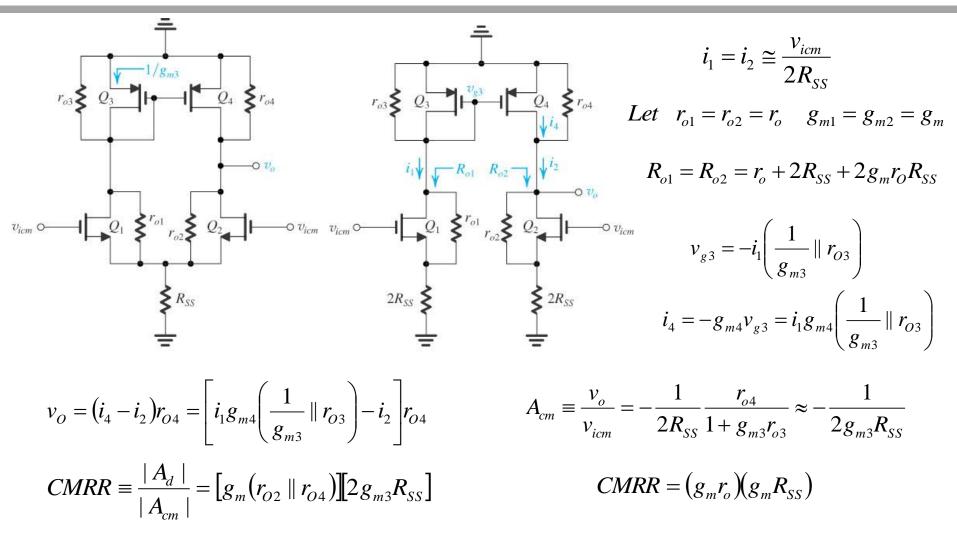
• 
$$|A_{v}| = G_{m}R_{out} = g_{m} [(2r_{O2}) || r_{O4}] \cong \frac{1}{2} g_{m}r_{o}$$

#### compared to p.21

$$A_{v} = \frac{g_{m2}}{2} [(2r_{O2}) || r_{O4}],$$

6dB improved

### Common-Mode Gain and CMRR

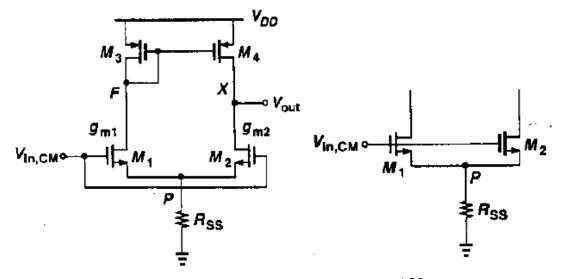


• The active-loaded MOS differential amplifier has a low  $A_{cm}$  and a high CMRR.

# Differential Pair with g<sub>m</sub> Mismatch

 Voltage change at P can be obtained by considering M<sub>1</sub> and M<sub>2</sub> as a single transistor in a SF configuration.

$$\Delta V_{P} = \Delta V_{in,CM} \frac{R_{SS}}{R_{SS} + \frac{1}{g_{m1} + g_{m2}}}$$



$$\Delta I_{D1} = g_{m1} \left( \Delta V_{in,CM} - \Delta V_P \right) = \frac{\Delta V_{in,CM}}{R_{SS} + \frac{1}{g_{m1} + g_{m2}}} \frac{g_{m1}}{g_{m1} + g_{m2}}, \quad \Delta I_{D2} = g_{m2} \left( \Delta V_{in,CM} - \Delta V_P \right) = \frac{\Delta V_{in,CM}}{R_{SS} + \frac{1}{g_{m1} + g_{m2}}} \frac{g_{m2}}{g_{m1} + g_{m2}}$$

$$\Delta I_{D4} = \Delta I_{D1} \left( \frac{1}{g_{m3}} \parallel r_{O3} \right) g_{m4}, \quad \Delta V_{out} = \left[ \Delta I_{D4} - \Delta I_{D2} \right] r_{O4} = \left[ \frac{g_{m1} \Delta V_{in,CM}}{1 + \left(g_{m1} + g_{m2}\right) R_{SS}} \frac{r_{O3}}{r_{O3} + \frac{1}{g_{m3}}} - \frac{g_{m2} \Delta V_{in,CM}}{1 + \left(g_{m1} + g_{m2}\right) R_{SS}} \right] r_{O4}$$

$$\Delta V_{out} = \frac{\Delta V_{in,CM}}{1 + (g_{m1} + g_{m2})R_{SS}} \frac{(g_{m1} - g_{m2})r_{O3} - g_{m2} / g_{m3}}{r_{O3} + \frac{1}{g_{m3}}} r_{O4}, \qquad \frac{\Delta V_{out}}{\Delta V_{in,CM}} \approx \frac{(g_{m1} - g_{m2})r_{O3} - g_{m2} / g_{m3}}{1 + (g_{m1} + g_{m2})R_{SS}}$$